

Appl. No. To be assigned.
Amdt. dated January 28, 2004
Preliminary Amendment

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-4. (Canceled)

5. (Currently amended) ~~A semiconductor manufacturing~~ An apparatus using plasma
~~using grounding cables, comprising:~~

~~a chamber~~ a reaction container where plasma is formed;

~~a plasma generating system is connected to the reaction container; and~~

~~a grounding cable earthing the apparatus, the grounding cable including:~~

~~a plasma generating source including a first electrode in the chamber, a first power
supplier and a first impedance matching device out of the chamber;~~

~~a bias source including a second electrode in the chamber, a second power supplier and a
second impedance matching device out of the chamber and~~

~~first, second, third, fourth and fifth grounding cables, each of the grounding cables
connected to the first and second power suppliers, the first and second impedance matching
devices and the chamber, respectively, each of the grounding cables including:~~

~~a first grounding wire;~~

~~a first outer cover surrounding the first grounding wire and made of an insulating
material;~~

~~a second grounding wire enclosing the first outer cover; and~~

~~a second outer cover surrounding the second grounding wire,~~

wherein the first and second grounding wires are connected in parallel.

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6. (Original) The apparatus according to claim 5, wherein the second grounding wire has a mesh structure.

7. (Original) The apparatus according to claim 5, wherein the first and second grounding wires include one of copper, copper coated with nickel and an alloy of copper and nickel.

8. (Original) The apparatus according to claim 5, wherein the first and second outer covers include polyvinyl chloride (PVC).

9. (New) The apparatus according to claim 5, wherein cross-sections of the first and second grounding wires have a rectangular shape.

10. (New) The apparatus according to claim 5, wherein cross-sections of the first and second grounding wires have a circular shape.

11. (New) The apparatus according to claim 5, wherein currents through the second grounding wire have higher frequencies than currents through the first grounding wire.

12. (New) The apparatus according to claim 11, wherein currents through the second grounding wire have frequencies more than about 100kHz flow.

13. (New) The apparatus according to claim 12, wherein currents through the first grounding wire have frequencies less than about 100kHz flow.

14. (New) The apparatus according to claim 5, wherein a substrate is treated with the plasma in the reaction container.

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15. (New) The apparatus according to claim 14, wherein a thin film is deposited on the substrate.

16. (New) The apparatus according to claim 14, wherein a thin film on the substrate is etched by the plasma.